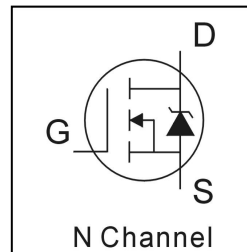


**N Channel High Voltage, Power MOSFET**

**Chip Specification**

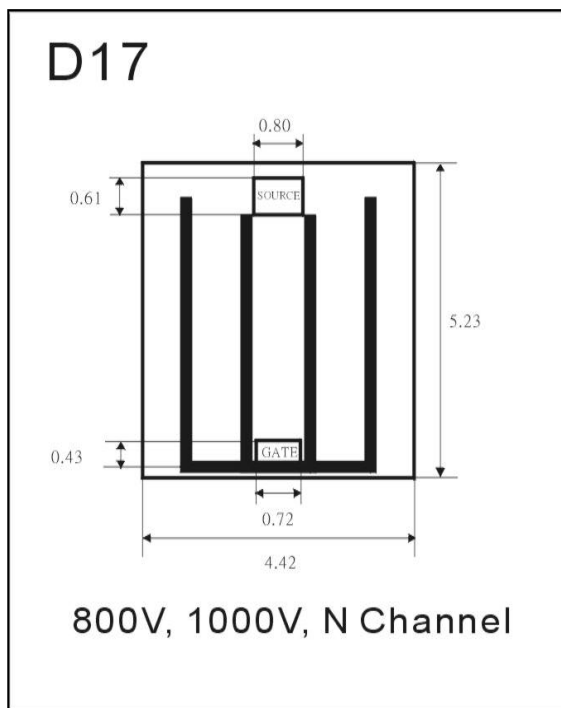
**General Description:**

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **150°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**
- \* **High Breakdown Voltage**



**Mechanical Data:**

<b>D17</b>	
Dimension	<b>4.42mm x 5.23mm</b>
Thickness:	<b>480 μm</b>
Metallization:	
Top :	<b>Al</b>
Backside :	<b>CrNiAg / Au</b>
Suggested Bonding Conditions:	
Die Mounting:	<b>Solder Perform</b>
<b>95/5 PbSn or 92.5/2.5/5 PbAgIn</b>	
Source Bonding Wire:	<b>10 mil Al</b>



**Absolute Maximum Rating**

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	900	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	4	Ω	VGS=10V, ID=2.2A
Continuous Drain current ( in target package)	ID@25°C	3.6	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	2.3	A	VGS=10V
Operation Junction	Tj	-55~175	°C	
Storage Temperature	TSTR	-55~175	°C	

**Target Device: IRFBF30**

TO-220AB

PD

125

W

@Tc=25°C

